

HiPerFET™ Power MOSFETs

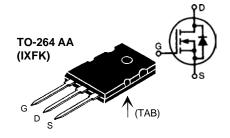
IXFK / IXFN 44 N50 IXFK / IXFN 48 N50

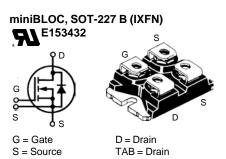
$oldsymbol{V}_{ exttt{DSS}}$	I _{D25}	R _{DS(on)}			
500 V	44 A	0.12 Ω			
500 V	48 A	0.12 Ω 0.10 Ω			
t _{rr} ≤ 250 ns					

N-Channel Enhancement Mode Avalanche Rated, High dv/dt, Low t,

Symbol	Test Conditions	Maximur IXFK	n Rating	
V _{DSS}	T _{_1} = 25°C to 150°C	500	500	V
V _{DGR}	$T_J = 25^{\circ}C$ to $150^{\circ}C$; $R_{GS} = 1 M\Omega$	500	500	V
V _{gs}	Continuous	±20	±20	V
V _{GSM}	Transient	±30	±30	V
I _{D25}	$T_{\rm c} = 25^{\circ}{\rm C}$ 44N50 48N50	44 48	44 48	A A
I _{DM}	$T_{\rm c} = 25^{\circ}$ C, 44N50 pulse width limited by $T_{\rm JM}$ 48N50	176 192	176 192	A A
I _{AR}	$T_{c} = 25^{\circ}C$	24	24	Α
E _{AR}	$T_{c} = 25^{\circ}C$	30	30	mJ
dv/dt	$\begin{split} &I_{_{S}} &\leq I_{_{DM}}, di/dt \leq 100 \; A/\mu s, V_{_{DD}} \leq V_{_{DSS}}, \\ &T_{_{J}} \leq 150 ^{\circ} C, R_{_{G}} = 2 \; \Omega \end{split}$	5	5	V/ns
$\overline{\mathbf{P}_{D}}$	T _C = 25°C	500	520	W
T		-55	+150	°C
T _{JM}			150	°C
T _{stg}		-55	+150	°C
T_L	1.6 mm (0.063 in) from case for 10 s	300	-	°C
V _{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \le 1 \text{ mA}$ $t = 1 \text{ s}$	-	2500 3000	V~ V~
M _d	Mounting torque Terminal connection torque	0.9/6	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		10	30	g

Symbol	Test Conditions	$(T_J = 25^{\circ}C, \text{ unless of} $ min.	 ristic Va se speci max.	
V _{DSS}	$V_{GS} = 0 \text{ V}, I_{D} = 1 \text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_{D} = 8 \text{ mA}$	2	4	V
I _{GSS}	$V_{GS} = \pm 20 V_{DC}, V_{DS} = 0$		±200	nA
I _{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0 V$	T _J = 25°C T _J = 125°C	400 2	μA mA
R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_{D} = 0.5 \bullet I_{D25}$	44N50 48N50	0.12 0.10	Ω Ω
	Pulse test, $t \le 300 \mu s$, duty	cycle d≤2%		





Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- · International standard packages
- Molding epoxies meet UL94 V-0 flammability classification
- SOT-227B miniBLOC with aluminium nitride isolation
- Low $R_{DS (on)}$ HDMOSTM process
- Unclamped Inductive Switching (UIS) rated
- · Fast intrinsic rectifier

Applications

- DC-DC converters
- Synchronous rectification
- · Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

- · Easy to mount
- · Space savings
- High power density



Symbol		Characteristic Values $(T_1 = 25^{\circ}C, \text{ unless otherwise specified})$		
	min.	typ.	max.	
g _{fs}	$V_{DS} = 10 \text{ V}; I_{D} = 0.5 \bullet I_{D25}, \text{ pulse test}$ 22	42		S
C _{iss} C _{oss} C _{rss}	$ V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz} $	8400 900 280		pF pF pF
t _{d(on)} t _r t _{d(off)}	$\begin{cases} V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \bullet V_{DSS}, I_{D} = 0.5 \bullet I_{D25} \\ R_{G} = 1 \Omega \text{ (External)}, \end{cases}$	30 60 100 30		ns ns ns
Q _{g(on)} Q _{gs} Q _{gd}	$ V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25} $	270 60 135		nC nC nC
$oldsymbol{R}_{ ext{thJC}} \ oldsymbol{R}_{ ext{thCK}}$	TO-264 AA TO-264 AA	0.15	0.25	K/W K/W
R _{thJC} R _{thCK}	miniBLOC, SOT-227 B miniBLOC, SOT-227 B	0.05	0.24	K/W K/W

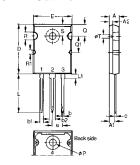
Source-Drain Diode

Characteristic Values

(T₁ = 25°C, unless otherwise specified)

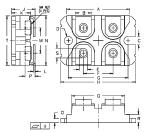
Symbol	Test Conditions min.	typ.	max.	,
I _s	V _{GS} = 0 V		48	Α
I _{SM}	Repetitive; pulse width limited by $T_{_{\rm JM}}$		192	Α
$\mathbf{V}_{\mathtt{SD}}$	$I_{_F}$ = 100 A, V $_{_{\rm GS}}$ = 0 V, Pulse test, t \leq 300 μs , duty cycle d \leq 2 %		1.5	V
t _{rr} Q _{RM} I _{RM}		TBD 20	250	ns μC A

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
Α	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
С	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
е	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
Р	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
Т	1.57	1.83	.062	.072

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millir	meter	Inches			
	Min.	Max.	Min. Max.			
A B	31.50	31.88	1.240	1.255		
С	4.09	4.29	0.161	0.169		
D E	4.09	4.29	0.161	0.169		
F	14.91	15.11	0.587	0.595		
G	30.12	30.30	1.186	1.193		
H	38.00	38.23	1.496	1.505		
J	11.68	12.22	0.460	0.481		
K	8.92	9.60	0.351	0.378		
L	0.76	0.84	0.030	0.033		
M	12.60	12.85	0.496	0.506		
N	25.15	25.42	0.990	1.001		
O	1.98	2.13	0.078	0.084		
PQ	4.95	5.97	0.195	0.235		
	26.54	26.90	1.045	1.059		
R S	3.94	4.42	0.155	0.174		
	4.72	4.85	0.186	0.191		
T	24.59	25.07	0.968	0.987		
U	-0.05	0.1	-0.002	0.004		

Fig. 1 Output Characteristics

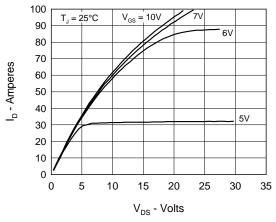


Fig. 3 $R_{DS(on)}$ vs. Drain Current

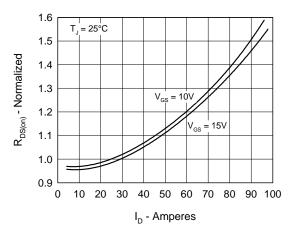


Fig. 5 Drain Current vs.

Case Temperature

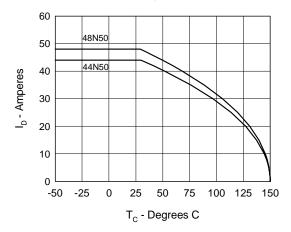


Fig. 2 Input Admittance

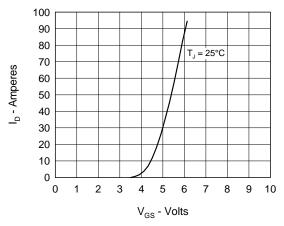


Fig. 4 Temperature Dependence of Drain to Source Resistance

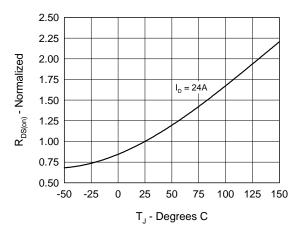


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

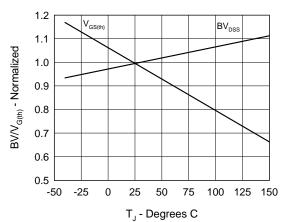
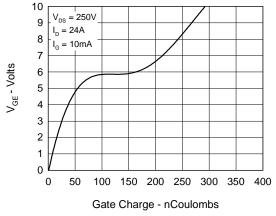


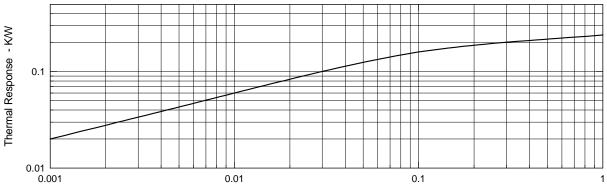
Fig.7 Gate Charge Characteristic Curve



to Drain Voltage 100 90 80 70 60 50 $T_J = 125^{\circ}C$ 40 30 T₁ = 25°C 20 10 0.00 0.25 0.50 0.75 1.00 1.25 $V_{\rm SD}$ - Volt

Fig.9 Source Current vs. Source 1.50

Fig.10 Transient Thermal Impedance



Time - Seconds

Fig.8 Capacitance Curves

